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Atty. Docket No. Serial No. INFORMATION DISCLOSURE NTI-019-5-1D Filed Herewith **CITATION Applicant** PIERRAT, Christophe PTO-1449 Group Filing Date Filed Herewith OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) CITATION EXAMINER'S INITIALS Balasinski, A., et al., "Comparison of Mask Writing Tools and Mask Simulations for 0.16um Devices", IEEE, SEMI Advanced Semiconductor Manufacturing Conference, pp. 372-377 (1999).

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PD	Cobb, N., et al., 'Fast, Low-Complexity Mask Design', SPIE, Vol. 2440, pp. 313-327, February 22-24; 1995.				
	Cobb, N., et al., "Experimental Results on Optical Proximity Correction With Variable Threshold Resist Model", SPIE, Vol. 3051, pp. 458-468, March 12-14, 1997.				
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